

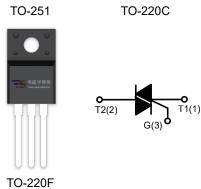
DESCRIPTION:

The BT138X-600E SCR series with the parallel resistor between Gate and Cathode are especially recommended for use on straight hair, igniter, anion generator, etc.





Symbol	Value	Unit
I _{T(RMS)}	12	А
V _{DRM} /V _{RRM}	600/800	V



ABSOLUTE MAXIMUM RATINGS

Parameter		Symbol	Value	Unit
Storage junction temperature range		T _{stg}	-40-150	$^{\circ}$
Operating junction temperature range		Tj	-40-125	$^{\circ}$
Repetitive peak off-state voltage(T _j =25℃)		V _{DRM}	600/800	V
Repetitive peak reverse voltage(T _j =25℃)		V_{RRM}	600/800	V
Non repetitive surge peak Off-state voltage		V _{DSM}	V _{DRM} + 100	V
Non repetitive peak reverse voltage		V _{RSM}	V _{RRM} + 100	V
RMS on-state current	TO-251/ TO-220C(Tc=95℃) TO-220F(Ins) (Tc=80℃)	- I _{T(RMS)}	12	А
Non repetitive surge peak on-state current (full cycle, F=50Hz)		Ітѕм	95	А
I ² t value for fusing (tp=10ms)		l ² t	45	A ² s



Critical rate of rise of on-state	I - II -III	- dl/dt	50	A/µs	
current(I _G =2×I _{GT})	IV		10	ΑνμS	
Peak gate current		I _{GM}	2	Α	
Average gate power dissipation		P _{G(AV)}	0.5	W	
Peak gate power		P _{GM}	5	W	

ELECTRICAL CHARACTERISTICS (T_j=25 °C unless otherwise specified)

Symbol	Test Condition	Quadrant		Value		Unit	
Symbol	rest Condition			D	E	F	Unit
lgт	V _D =12V R _L =33Ω	I - II -III	MAX	5	10	25	mA
		IV		10	25	70	
V _G T		ALL	MAX		1.5		V
V _{GD}	$V_D=V_{DRM}T_j=125$ °C RL=3.3KΩ	ALL	MIN	0.2		V	
IL	I _G =1.2I _{GT}	I - III	MAX	15	30	40	mA
		II - IV		20	40	80	
Ін	I _T =100mA		MAX	10	25	30	mA
dV/dt	V _D =2/3V _{DRM} Gate Open T _j =125℃		MIN	20	50	50	V/µs

STATIC CHARACTERISTICS

Symbol	Parameter		Value(MAX)	Unit
V _{TM}	I _{тм} =15A tp=380µs	Tj=25℃	1.6	V
IDRM	- V _D =V _{DRM} V _R =V _{RRM}	Tj=25℃	5	μA
I _{RRM}		Tj=125℃	1	mA

THERMAL RESISTANCES

Symbol	Parameter	Value	Unit	
Rth(j-c)	junction to case(AC)	TO-220C	1.4	°C/W
		TO-220F(Ins)	2.5	
		TO-251	1.7	



FIG.1: Maximum power dissipation versus RMS on-state current

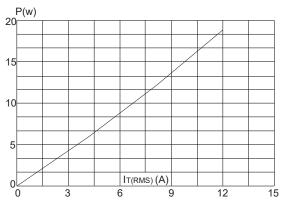


FIG.3: Surge peak on-state current versus number of cycles

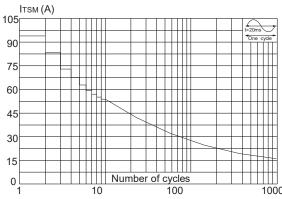


FIG.2: RMS on-state current versus case temperature

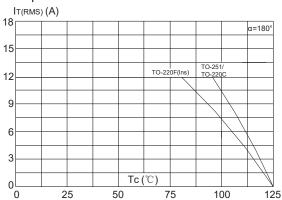
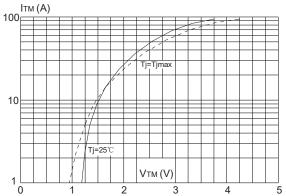


FIG.4: On-state characteristics (maximum values)





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FIG.5: Non-repetitive surge peak on-state current for a sinusoidal pulse with width tp<20ms, and corresponging value of $I^2t(I-II-III:dI/dt < 50A/\mu s; IV:dI/dt < 10A/\mu s)$

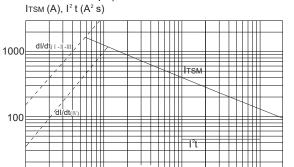


FIG.7: Relative variations of holding current versus junction temperature

tp(ms)

1

10 20

0.1

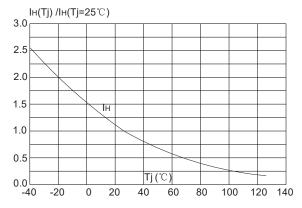


FIG.6: Relative variations of gate trigger current versus junction temperature

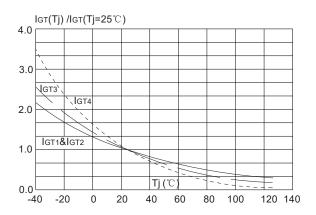


FIG.8: Relative variations of latching current versus junction temperature

